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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

Application Number	
Filing Date	
First Named Inventor	Nathan David Hiller
Art Unit	
Examiner Name	
Attorney Docket Number	

U. S. PATENT DOCUMENTS

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**Examiner
Signature**

Date Considered

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Sheet	2	of	2	Attorney Docket Number	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		L. ESAKI et al, Superlattice and Negative Differential Conductivity in Semiconductors, IBM J. of Research and Development, volume 14, page 61, 1970.	
		M. I. OVSYANNIKOV et al, Periodic Semiconductor Structures, Soviet Physics - Semiconductors, volume 4, no. 12, page 1919, 1970.	
		K.PLOOG et al, The Use of Si and Be Impurities for Novel Periodic Doping Structures in GaAs Grown by Molecular Beam Epitaxy, J. Electrochemical Soc., vol. 128, pg. 400, 1981.	
		Y. YAMAUCHI et al, Photoluminescence of InP Doping Superlattice Grown by Vapor Phase Epitaxy, Japanese Journal of Applied Physics, volume 23, number 10, page L785, 1984.	
		W. JANTSCH et al, Anomalous Transport in PbTe Doping Superlattices, Applied Physics Letters, volume 47, number 7, page 738, 1985.	
		M. KITAMURA et al, Doping Superlattices in GaP, Journal of Applied Physics, volume 61, number 4, page 1533, 1987.	
		L. C. KIMERLING, New Developments in Defect Studies in Semiconductors, IEEE Transactions on Nuclear Science, volume NS-23, number 6, page 1497, Dec. 1976.	
		L.C. KIMERLING et al, Electronically Controlled Reactions of Interstitial Iron in Silicon, Physica 116B, page 297, 1983.	

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